

ABSTRACT OF THE DISCLOSURE

A surface emitting semiconductor laser is formed from a substrate having a first mirror formed thereon. The first mirror includes semiconductor layers of a first conductivity type. A second mirror is formed over the substrate and includes semiconductor layers of a second conductivity type. An active region is disposed between the first and second mirrors, with a current confining layer being disposed between the first and second mirrors. A compound semiconductor layer is formed over the second mirror and an electrode is formed on the compound semiconductor layer. A protective film covers the compound semiconductor layer and partially covers the electrode. The electrode is formed by a lift-off process and uses an opening-pattern that is formed by plasma ashing.